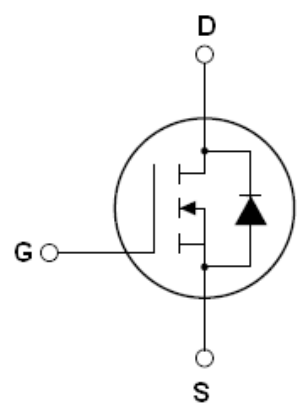
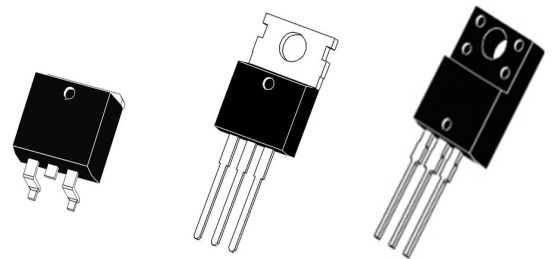


QIAOXIN N-Channel Super Junction Power MOSFET III

<p>General Description</p> <p>The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.</p> <p>Features</p> <ul style="list-style-type: none"> ● Optimized body diode reverse recovery performance ● Low on-resistance and low conduction losses ● Small package ● Ultra Low Gate Charge cause lower driving requirements ● 100% Avalanche Tested ● ROHS compliant <p>Application</p> <ul style="list-style-type: none"> ● Power factor correction (PFC) ● Switched mode power supplies(SMPS) ● Uninterruptible Power Supply (UPS) ● LLC Half-bridge 	<table border="1" style="width: 100%; border-collapse: collapse; margin-bottom: 10px;"> <tr> <td style="padding: 2px;">V_{DS}</td> <td style="padding: 2px;">650</td> <td style="padding: 2px;">V</td> </tr> <tr> <td style="padding: 2px;">$R_{DS(ON) MAX}$</td> <td style="padding: 2px;">180</td> <td style="padding: 2px;">mΩ</td> </tr> <tr> <td style="padding: 2px;">I_D</td> <td style="padding: 2px;">21</td> <td style="padding: 2px;">A</td> </tr> </table> <div style="text-align: center;">  <p>Schematic diagram</p> </div>	V_{DS}	650	V	$R_{DS(ON) MAX}$	180	mΩ	I_D	21	A
V_{DS}	650	V								
$R_{DS(ON) MAX}$	180	mΩ								
I_D	21	A								

Package Marking And Ordering Information

Device	Device Package	Marking
VCRR65TF180	TO-220	VCRR65TF180
VCRR65TF180F	TO-220F	VCRR65TF180F
VCRR65TF180D	TO-263	VCRR65TF180D



TO-263

TO-220

TO-220F

Table 1. Absolute Maximum Ratings ($T_C=25^\circ C$)

Parameter	Symbol	VCRR65TF180D VCRR65TF180	VCRR65TF180F	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	650		V
Gate-Source Voltage ($V_{DS}=0V$), AC ($f>1$ Hz)	V_{GS}	± 30		V
Continuous Drain Current at $T_C=25^\circ C$	$I_{D(DC)}$	21	21*	A
Continuous Drain Current at $T_C=100^\circ C$	$I_{D(DC)}$	13.2	13.2*	A
Pulsed drain current ^(Note 1)	$I_{DM(pluse)}$	84	84*	A
Maximum Power Dissipation($T_C=25^\circ C$)	P_D	188	33.8	W
Derate above $25^\circ C$		1.5	0.27	W/ $^\circ C$
Single pulse avalanche energy ^(Note 2)	E_{AS}	441		mJ
Avalanche current ^(Note 1)	I_{AR}	10.5		A
Repetitive Avalanche energy , t_{AR} limited by T_{Jmax} ^(Note 1)	E_{AR}	0.7		mJ

Parameter	Symbol		Unit
Drain Source voltage slope, $V_{DS} \leq 480V$,	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS} \leq 480V, I_{SD} < I_D$	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+150	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol			Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	0.66	3.69	°C/W
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62.5	80	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	650			V
Zero Gate Voltage Drain Current($T_C=25^\circ C$)	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$			2	μA
Zero Gate Voltage Drain Current($T_C=125^\circ C$)	I_{DSS}	$V_{DS}=650V, V_{GS}=0V$			100	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3	3.5	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=10.5A$		150	180	m Ω
Dynamic Characteristics						
Forward Transconductance	g_{FS}	$V_{DS} = 20V, I_D = 10.5A$		16		S
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$		2250		PF
Output Capacitance	C_{oss}			83		PF
Reverse Transfer Capacitance	C_{rss}			1.6		PF
Total Gate Charge	Q_g	$V_{DS}=480V, I_D=21A,$ $V_{GS}=10V$		36		nC
Gate-Source Charge	Q_{gs}			14		nC
Gate-Drain Charge	Q_{gd}			8.5		nC
Switching times						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=380V, I_D=11A,$ $R_G=4\Omega, V_{GS}=10V$		11		nS
Turn-on Rise Time	t_r			6		nS
Turn-Off Delay Time	$t_{d(off)}$			61		nS
Turn-Off Fall Time	t_f			4.5		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	$T_C=25^\circ C$			21	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				84	A
Forward on voltage	V_{SD}	$T_J=25^\circ C, I_{SD}=21A, V_{GS}=0V$		0.9	1.3	V
Reverse Recovery Time	t_{rr}	$T_J=25^\circ C, I_F=11A, di/dt=100A/\mu s$		160		nS
Reverse Recovery Charge	Q_{rr}			1.4		μC
Peak Reverse Recovery Current	I_{rrm}			17		A

Notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area for TO-220/TO-263

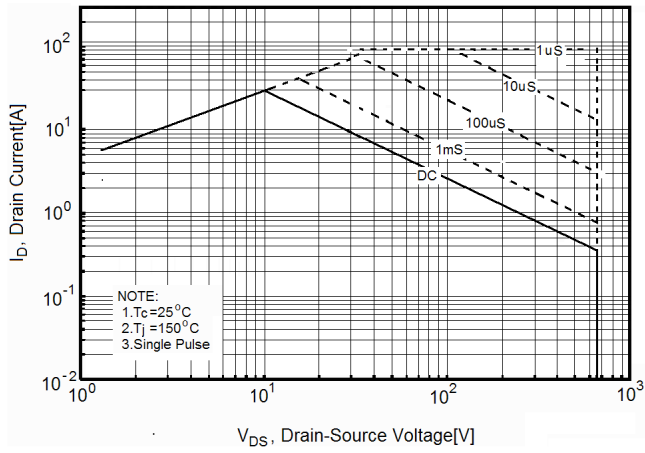


Figure2. Safe operating area for TO-220F

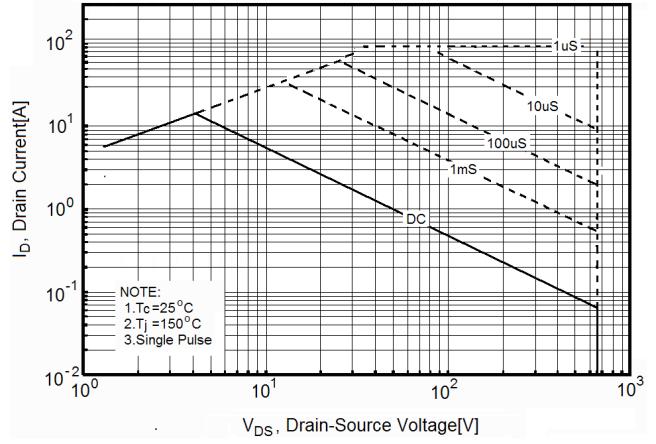


Figure3. Source-Drain Diode Forward Voltage

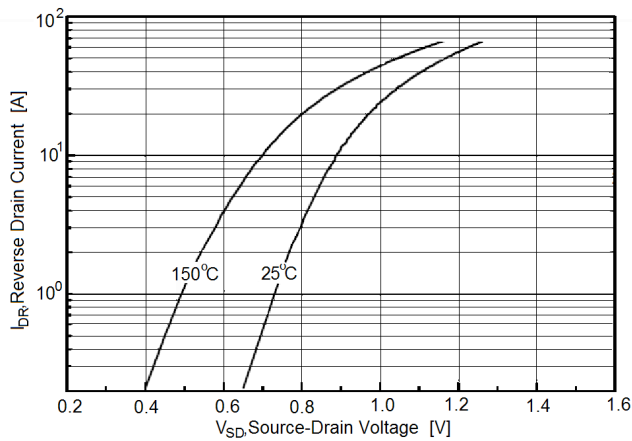


Figure4. Output characteristics

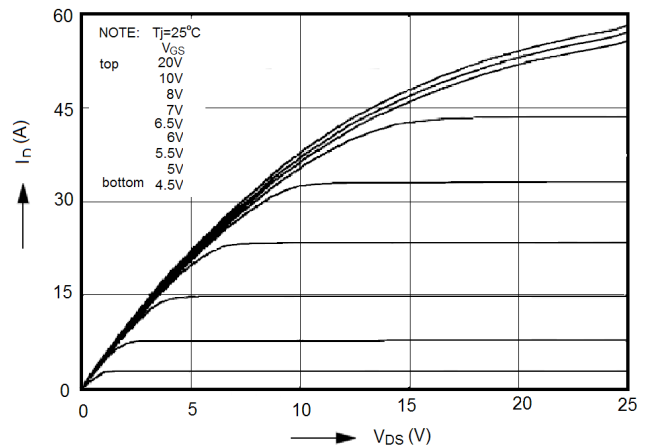


Figure5. Transfer characteristics

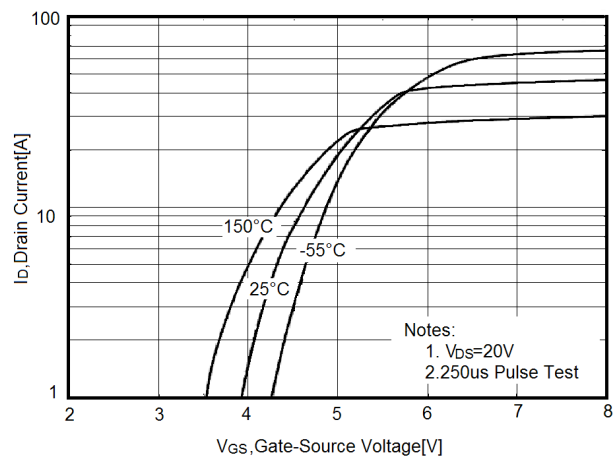


Figure6. Static drain-source on resistance

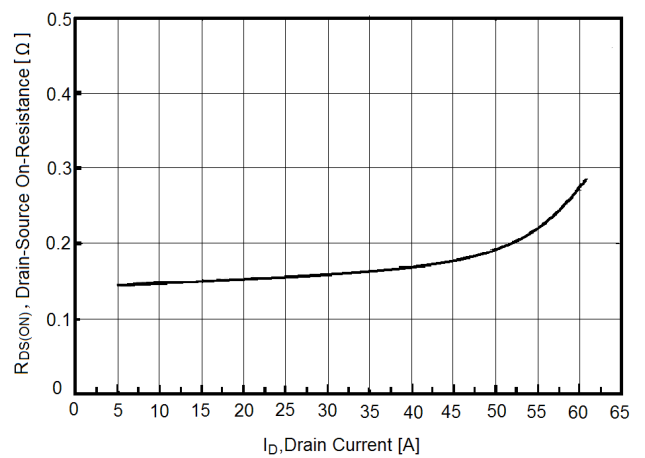


Figure7. $R_{DS(ON)}$ vs Junction Temperature

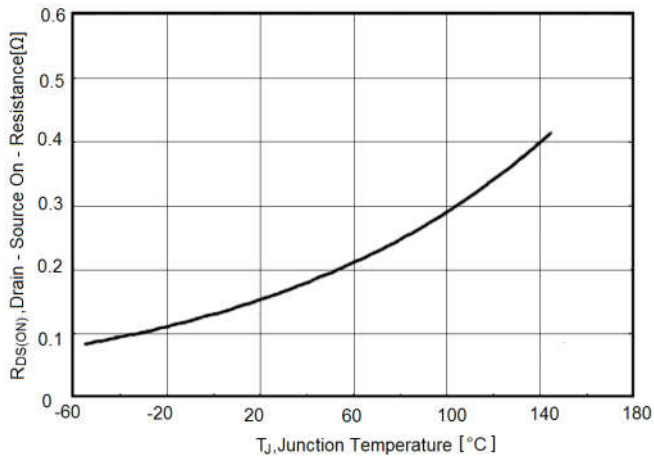


Figure8. BV_{DSS} vs Junction Temperature

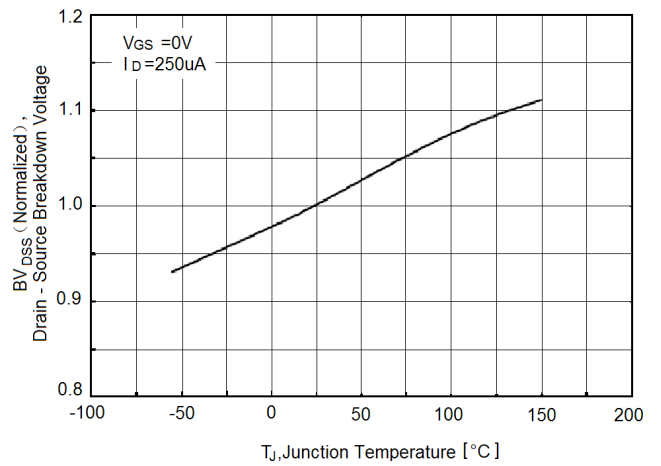


Figure9. Maximum I_D vs Junction Temperature

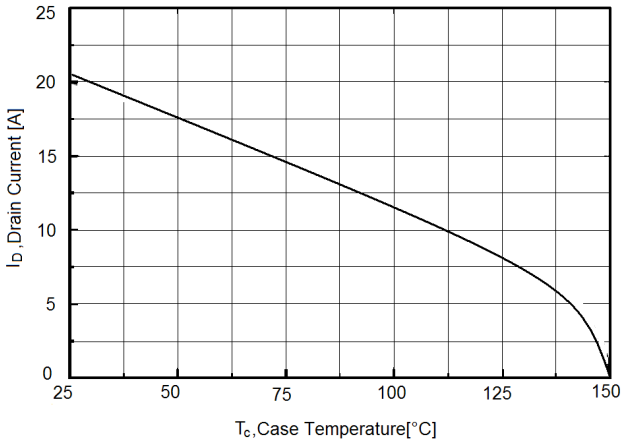


Figure10. Transient Thermal Impedance for TO-220

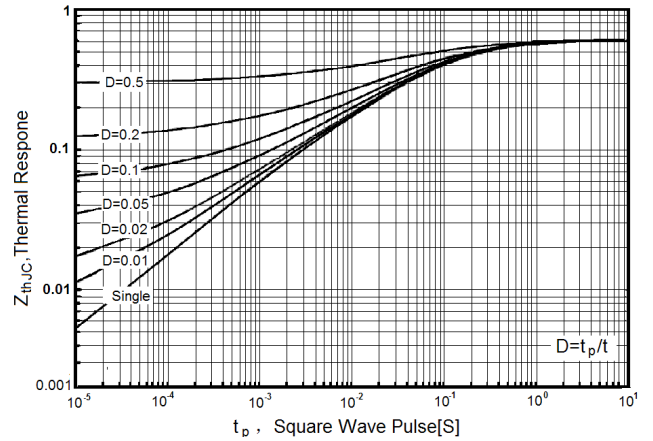


Figure11. Transient Thermal Impedance for TO-220F

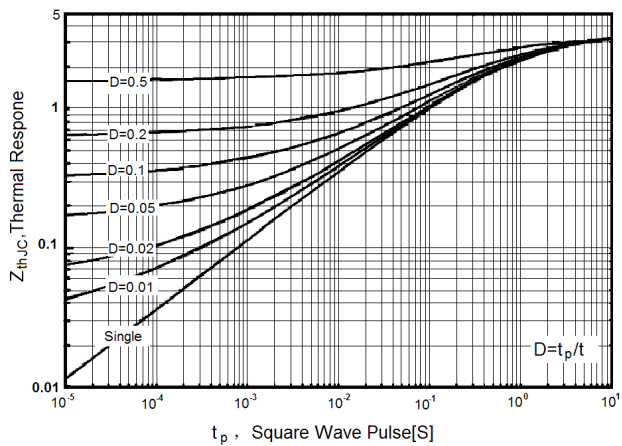


Figure12. Gate charge waveforms

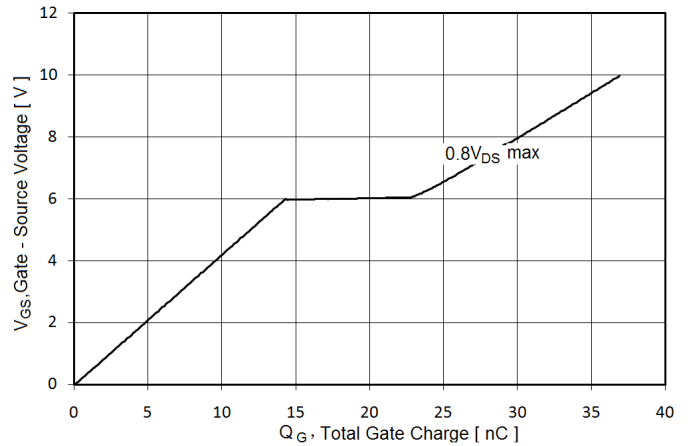
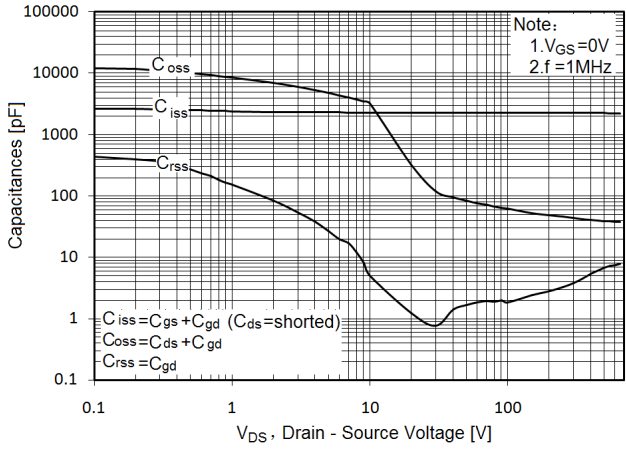
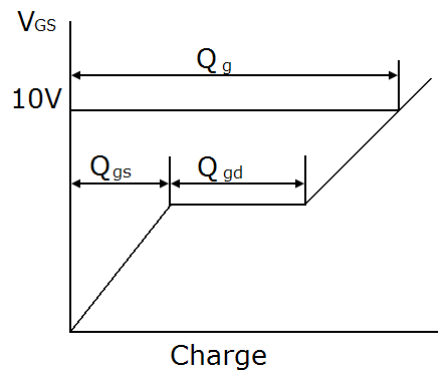
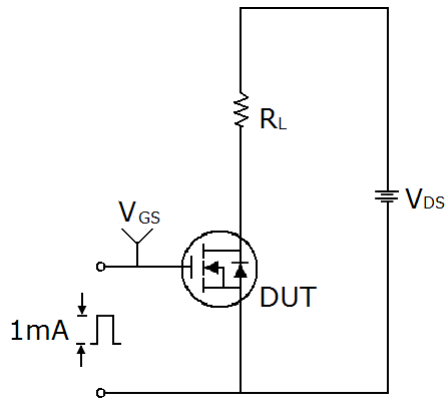


Figure13. Capacitance

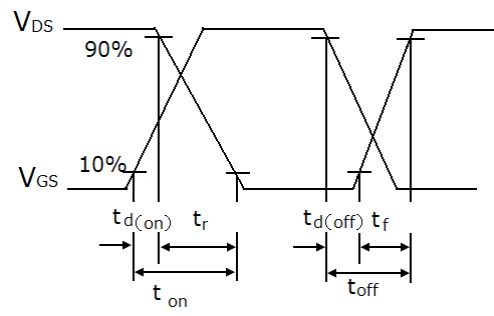
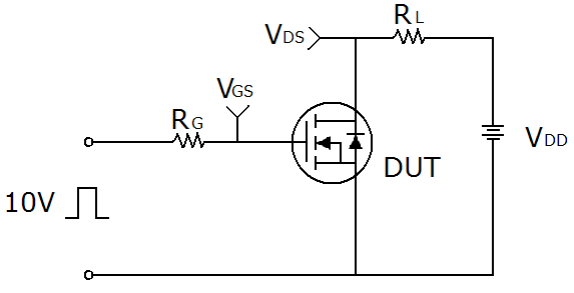


Test circuit

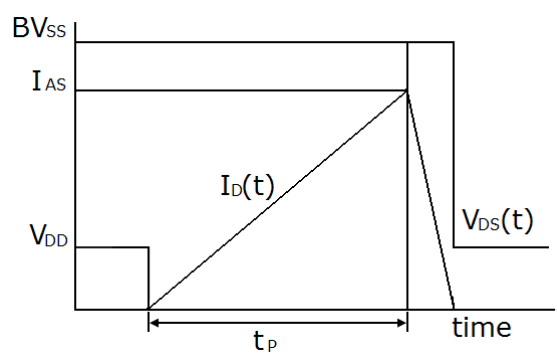
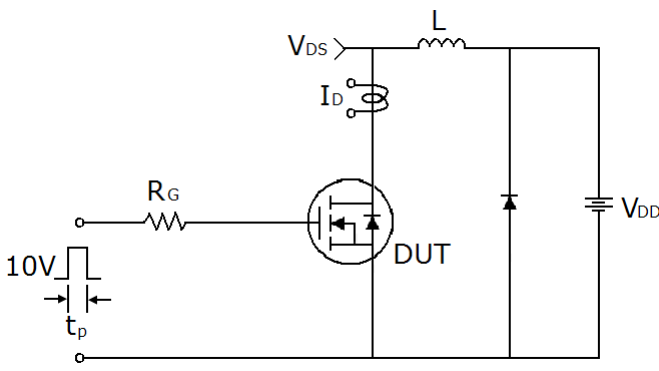
1) Gate charge test circuit & Waveform



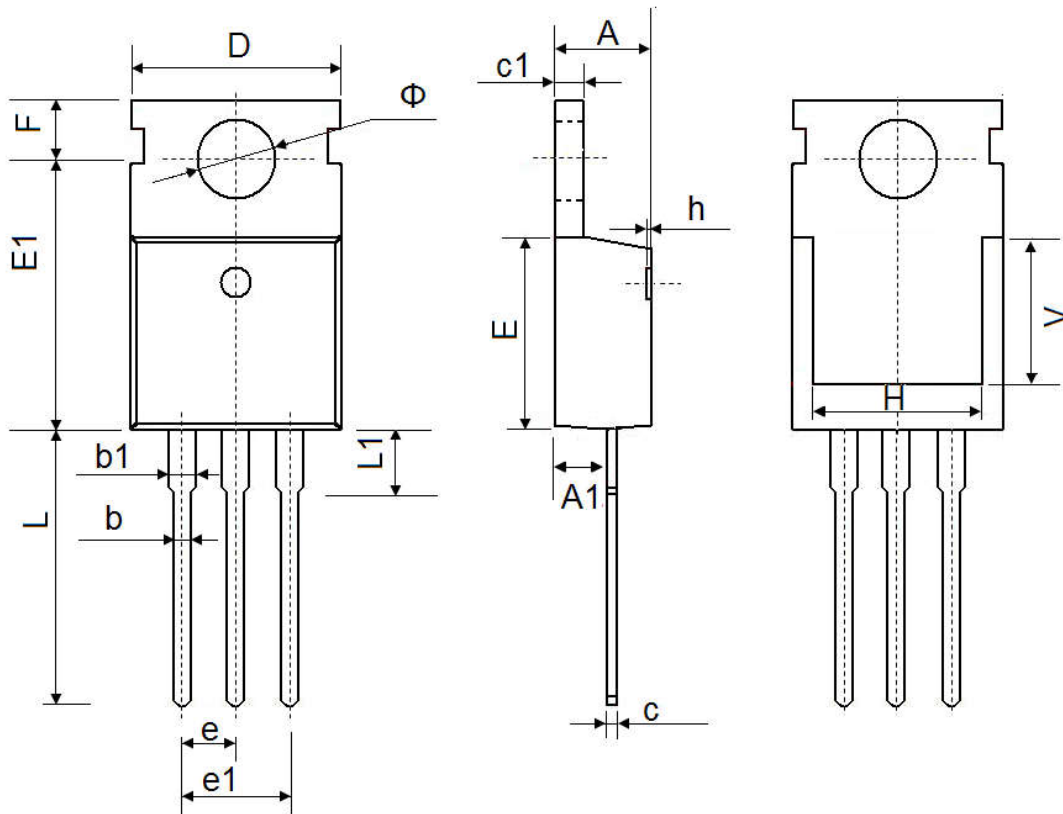
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

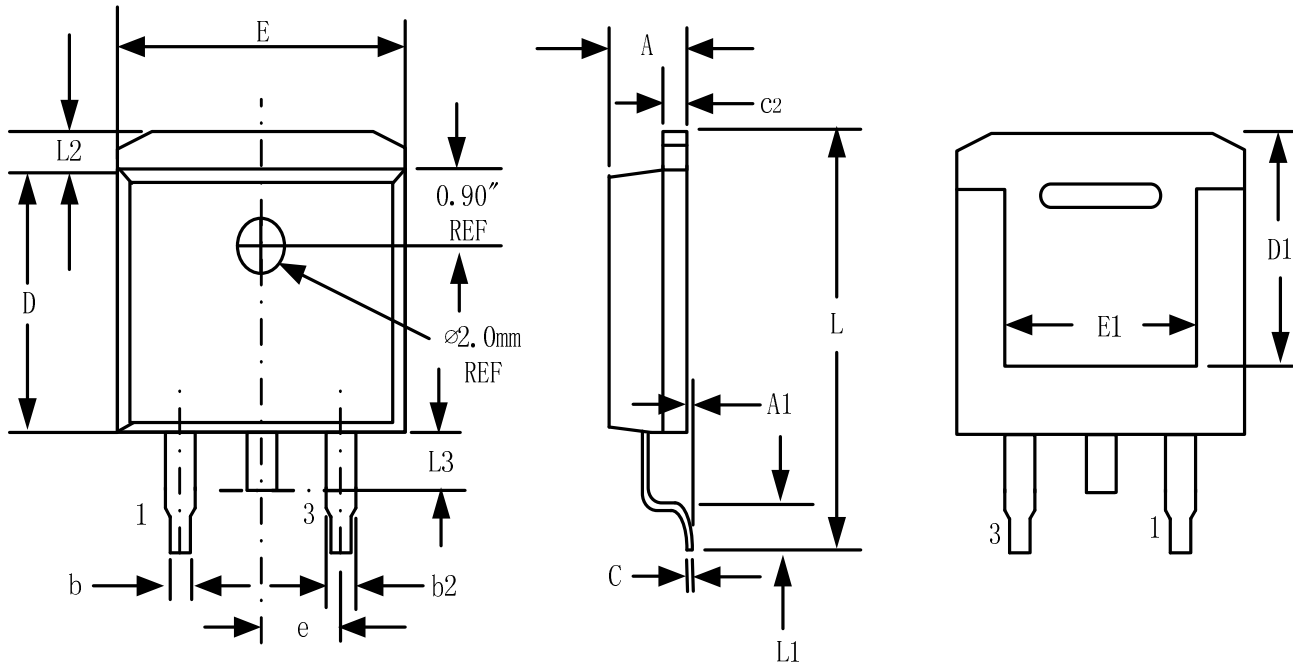


TO-220-3L-C Package Information



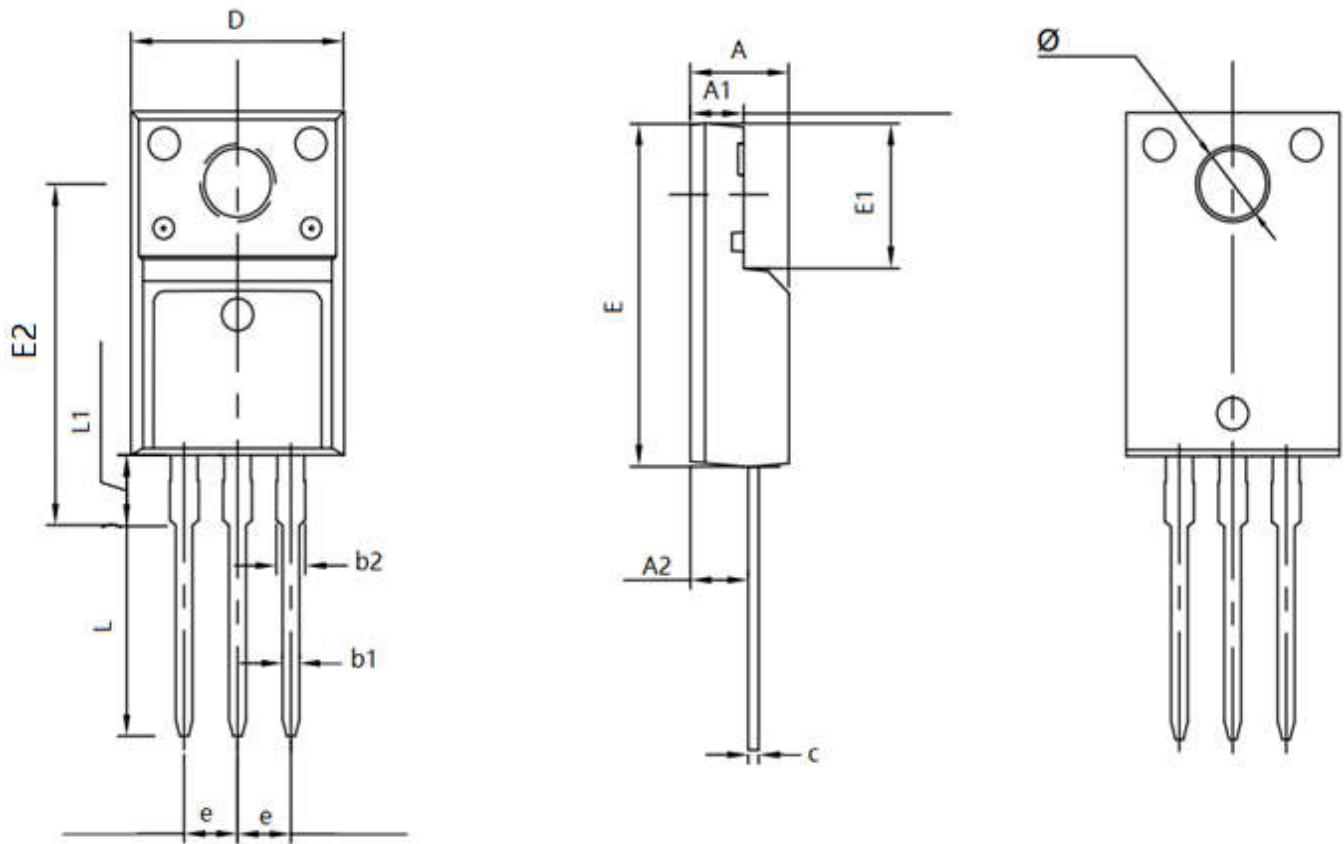
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

TO-263-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.57	0.170	0.180
A1	-	0.25		0.010
b	0.71	0.94	0.028	0.037
b2	1.15	1.40	0.045	0.055
c	0.46	0.61	0.018	0.024
c2	1.22	1.40	0.048	0.055
D	8.89	9.40	0.350	0.370
D1	8.01	8.23	0.315	0.324
E	10.04	10.28	0.395	0.405
E1	7.88	8.08	0.310	0.318
e	2.54 BSC		0.100 BSC	
L	14.73	15.75	0.580	0.620
L1	2.29	2.79	0.090	0.110
L2	1.15	1.39	0.045	0.055
L3	1.27	1.77	0.050	0.070

TO-220F Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.500	4.900	0.177	0.193
A1	2.340	2.740	0.092	0.108
A2	2.560	2.960	0.101	0.117
b1	0.700	0.900	0.028	0.035
b2	1.180	1.580	0.046	0.062
c	0.400	0.600	0.016	0.024
D	9.960	10.360	0.392	0.408
E	15.670	15.970	0.617	0.629
E1	6.500	6.900	0.256	0.272
E2	15.500	16.100	0.610	0.634
e	2.540 TYP		0.100 TYP	
φ	3.080	3.280	0.121	0.129
L	12.640	13.240	0.498	0.521
L1	3.030	3.430	0.119	0.135

ATTENTION

QIAOXIN assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all QIAOXIN products described or contained herein. QIAOXIN products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. QIAOXIN reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.